

IN THE CLAIMS

Please cancel claims 1-7 without prejudice.

Please amend the following claims which are pending in the present application:

1-7. (Cancelled)

8. (Previously amended) A wafer comprising:

a layer of solid diamond;

a final monocrystalline semiconductor film on the layer of solid diamond;

and

a layer of monocrystalline semiconductor material directly on the final monocrystalline semiconductor film with a boundary defined between the final monocrystalline semiconductor film and the layer of monocrystalline semiconductor material for purposes of shearing the layer of monocrystalline semiconductor material from the final monocrystalline semiconductor film.

9. (Original) The wafer of claim 8 wherein the layer of solid diamond is at least 200 mm wide.

10. (Original) The wafer of claim 9 wherein the layer of monocrystalline semiconductor material is at least 200 mm wide.

11. (Original) The wafer of claim 10 wherein the layer of monocrystalline semiconductor material is a layer of monocrystalline silicon.

12. (Currently amended) A singulated die comprising:

a layer of solid diamond having an exposed lower surface; ~~and~~

a layer of monocrystalline semiconductor material on the layer of solid diamond; and

an integrated circuit on a side of the layer of monocrystalline semiconductor material opposing the layer of solid diamond.

13. (Previously amended) The singulated die of claim 12 further comprising:

a layer of monocrystalline semiconductor material on the layer of solid diamond, the integrated circuit being formed on the layer of monocrystalline semiconductor material.

14. (Original) The singulated die of claim 13 wherein the layer of monocrystalline semiconductor material is a layer of monocrystalline silicon.

15. (Currently amended) The singulated die of claim 14 further comprising:

a layer of polysilicon ~~on~~ between the layer of monocrystalline silicon, ~~the layer of monocrystalline silicon being located on the layer of polysilicon and the~~

cancel.
layer of solid diamond.

16. (Original) The singulated die of claim 12 further comprising:
a plurality of contacts on the integrated circuit.

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17. (Previously amended) The singulated die of claim 12 wherein the die has a rectangular outline when viewed from above.

18-24. (Cancelled)

25. (Currently amended) A wafer, comprising:

a layer of solid diamond having a thickness of less than 150 microns; ~~and~~

a layer of monocrystalline semiconductor material on the layer of solid diamond; and

a plurality of integrated circuits in rows and columns on the layer of monocrystalline semiconductor material, with the layer of monocrystalline semiconductor material between the layer of solid diamond and the rows and columns of integrated circuits.

26. (Cancelled)

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27. (Currently amended) The wafer of claim ~~26~~ 25 wherein a layer of

By
encl. monocrystalline semiconductor material is a layer of silicon.
